



5303D

Preliminary

NPN SILICON TRANSISTOR

HIGH VOLTAGE NPN TRANSISTOR WITH DIODE

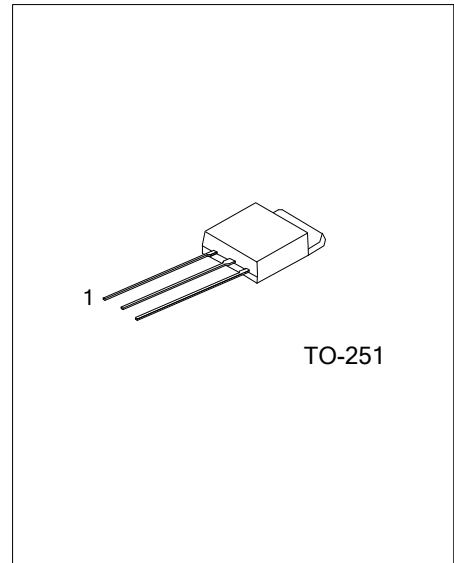
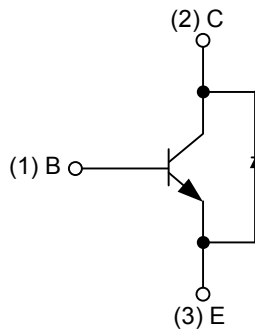
■ DESCRIPTION

The UTC **5303D** is a high voltage silicon triple diffused type NPN transistor with diode. This chip is built in free-wheeling diode, making efficient anti-saturation operation.

■ FEATURES

- * Not Necessary to Interest an h_{FE} Value
- * Need Very Low Base Drive
- * Can Be Used In Half Bridge Light Ballast Application

■ INTERNAL SCHEMATIC DIAGRAM



Lead-free: 5303DL
Halogen-free: 5303DG

■ ORDERING INFORMATION

Ordering Number			Package	Pin Assignment			Packing
Normal	Lead Free Plating	Halogen Free		1	2	2	
5303D-TM3-T	5303DL-TM3-T	5303DG-TM3-T	TO-251	B	C	E	Tube

<p>5303DL-TM3-T</p>	<p>(1) T: Tube (2) TM3: TO-251 (3) G: Halogen Free, L: Lead Free, Blank: Pb/Sn</p>
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■ ABSOLUTE MAXIMUM RATING (Ta = 25°C, unless otherwise noted)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V _{CBO}	700	V
Collector-Emitter Voltage	V _{CEO}	400	V
Emitter-Base Voltage	V _{EBO}	10	V
Collector Current	I _C	2	A
Collector Peak Current (tp<5ms)	I _{CM}	4	A
Base Current	I _B	1	A
Base Peak Current (tp<5ms)	I _{BM}	2	A
Collector Dissipation (T _C ≤25°C)	P _C	25	W
Maximum Operating Junction Temperature	T _J	+150	°C
Storage Temperature Range	T _{STG}	-65~+150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ _{JA}	100	°C/W
Junction to Case	θ _{JC}	6.25	°C/W

■ ELECTRICAL CHARACTERISTICS (Ta = 25°C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Collector-Base Voltage	BV _{CBO}	I _C = 1mA, I _B = 0	700			V
Collector-Emitter Breakdown Voltage (Note)	BV _{CEO}	I _C = 10mA, I _E = 0	400			V
Emitter-Base Breakdown Voltage	BV _{EBO}	I _E = 1mA, I _C = 0	10			V
Collector Cutoff Current	I _{CBO}	V _{CB} = 700V, I _E = 0			1	μA
Emitter Cutoff Current	I _{EBO}	V _{EB} = 9V, I _C = 0			1	μA
ON CHARACTERISTICS						
DC Current Gain	h _{FE1}	V _{CE} = 5V, I _C = 10mA	10			
	h _{FE2}	V _{CE} = 5V, I _C = 400mA	10		30	
	h _{FE3}	V _{CE} = 5V, I _C = 1A	5			
Collector-Emitter Saturation Voltage (Note)	V _{CE(SAT1)}	I _C = 0.5A, I _B = 0.1A			0.5	V
	V _{CE(SAT2)}	I _C = 1A, I _B = 0.25A		1.1	1.5	V
Base-Emitter Saturation Voltage (Note)	V _{BE(SAT)}	I _C = 0.5A, I _B = 0.1A			1.1	V
	V _{BE(SAT2)}	I _C = 1A, I _B = 0.25A			1.2	V
SWITCHING CHARACTERISTICS						
Turn On Time	t _{ON}	V _{CC} = 250V, I _C = 1A,		0.15	0.3	μS
Storage Time	t _{STG}	I _{B1} = I _{B2} = 0.2A, t _p = 25μS Duty		0.5	0.9	μS
Fall Time	t _F	Cycle < 1%		0.2	0.4	μS
Diode						
Forward Voltage Drop	V _F	I _C = 1A			1.4	V
Fall Time	t _F	I _C = 1A			800	μS

Note: Pulsed duration = 300μS, duty cycle ≤ 2%

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